

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1705	(GaAs GaP InAs InP) with nitride adj (film layer cover\$3 coat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 11:23
S2	33	(GaAs GaP InAs InP) with nitride adj (film layer cover\$3 coat\$3) with vapor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:21
S3	63	(III-V GaAs GaP InAs InP) with nitride adj (film layer cover\$3 coat\$3) with vapor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 13:31
S4	12	(III-V GaAs GaP InAs InP) with nitride adj (film layer cover\$3 coat\$3) with vapor and beam adj epitaxy	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 18:34
S5	34	bhat.in. and III-V	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 18:35
S7	62	bhat.in. and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 18:35
S8	35	bhat.in. and nitride and vapor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 18:35
S9	5	(III-V adj nitride) adj (film layer cover\$3 coat\$3) with vapor with heat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 19:07
S10	16	(III-V adj nitride) adj (film layer cover\$3 coat\$3) with vapor and heat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 19:09
S11	0	(III-V adj nitride) adj (film layer cover\$3 coat\$3) with vapor and heat\$3 with atmosphere with v near2 group	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 19:10
S12	1	(III-V adj nitride) and heat\$3 with atmosphere with v near2 group	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 19:11
S13	21	bhat.in. and rajaram.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 19:12

S14	1	bhat.in. and rajaram.in. and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 19:12
S15	10	bhat.in. and rajaram.in. and heat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 19:16
S17	124	hydrogen with arsine with heat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 19:19
S18	4	hydrogen with arsine with heat\$3 with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 19:20
S19	4	(hydrogen "H.sub.2") with arsine with heat\$3 with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/26 19:20
S24	618	(III-V GaAs GaP InAs InP) and heat\$3 with atmosphere near5 (N as P Sb Bi)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/04 16:17
S25	278	(III-V GaAs GaP InAs InP) with substrate and heat\$3 with atmosphere near5 (N as P Sb Bi)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/04 16:17
S26	136	(III-V GaAs GaP InAs InP) with heat\$3 with atmosphere near5 (N as P Sb Bi)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 08:36
S27	17	("4713354").URPN.	USPAT	OR	ON	2005/05/04 16:45
S29	95	(III-V GaAs GaP InAs InP) with OMCvd	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/04 17:00
S30	32	(III-V GaAs GaP InAs InP) with OMCvd and cool\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/04 17:02
S31	26	("5453405").URPN.	USPAT	OR	ON	2005/05/04 17:02
S32	90	OMCvd and cool\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/04 17:02
S33	8	OMCvd with cool\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/04 17:10

S34	0	(III-V GaAs GaP InAs InP) adj nitride with cool\$3 with atmosphere	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 09:22
S35	272	nitride with cool\$3 with atmosphere	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/04 17:12
S36	30	nitride with cool\$3 with atmosphere and (Cvd vapor adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/04 17:15
S37	2	nitride with cool\$3 with atmosphere with decomposition	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/04 17:21
S38	20	nitride with cool\$3 with atmosphere with (ammonia dimethylhydrazine trimethylamine, alkylamine)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/04 17:28
S39	23	nitride same cool\$3 with atmosphere near3 (ammonia dimethylhydrazine trimethylamine alkylamine)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/04 17:28
S45	85	(III-V) with buffer adj layer with nitride and MOCvd and LED	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 08:59
S46	198	(III-V) same buffer adj layer with nitride and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 08:59
S47	110	(III-V) same buffer adj layer with nitride and semiconductor and epitaxy	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 08:59
S48	20	(III-V) near3 substrate same buffer adj layer with nitride and semiconductor and epitaxy	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 09:01
S49	28	(GaAs GaP InAs InP) near3 substrate same buffer adj layer with nitride and semiconductor and epitaxy	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 09:22
S50	167	(GaAs GaP InAs InP) near3 substrate and buffer adj layer with nitride and semiconductor with LED	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 09:04

S51	62	(GaAs GaP InAs InP) near3 substrate and buffer adj layer near3 nitride and semiconductor with LED	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 09:04
S52	6	(III-V GaAs GaP InAs InP) adj substrate with (III-V GaAs GaP InAs InP) adj nitride and vapor adj deposition and buffer adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 15:53
S53	3	"6709703".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 15:55
S54	2	("4047496" "6218280").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/05 15:57
S55	21	(GaN InN AlN) near2 vapor same semiconductor with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:57
S56	15	(GaN InN AlN) near2 gas same semiconductor with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:43
S57	110	nitrogen adj source with semiconductor with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:36
S58	8	nitrogen adj source with semiconductor with nitride with (III-V GaAs GaP InAs InP)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:42
S59	0	III adj nitrogen adj vapor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:43
S60	45	(GaN InN AlN (aluminum mindium gallium) adj nitride) near2 vapor same semiconductor with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:45
S61	233	(GaN InN AlN (aluminum mindium gallium) adj nitride) near2 vapor and vapor adj deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:45
S62	116	(GaN InN AlN (aluminum mindium gallium) adj nitride) near2 vapor same vapor adj deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:45

S63	4	(GaN InN AlN (aluminum indium gallium) adj nitride) adj vapor same vapor adj deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:46
S64	5	dilute adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:57
S65	5	(GaN InN AlN) with single adj source adj precursor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:58
S66	3	single adj source adj precursor with III-v	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:57
S67	26	single adj source adj precursor with organo\$2metal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 16:59
S68	13	single adj source adj precursor with organo\$2metal\$4 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 17:15
S69	24	427/69.ccls. and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 17:17
S70	66	427/255.23.ccls. and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 17:20
S71	51	427/255.34.ccls. and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 17:21
S72	14	427/255.34.ccls. and 427/255.394.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 17:24
S73	523	427/255.394.ccls. and (Ga Al In)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 17:25
S74	61	427/255.394.ccls. and (Ga Al In) near2 nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/05 17:25

S75	16	(Ga Al In Gallium Aluminum Indium) near2 amine with deposition and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/06 10:41
S76	16	(Gallium Aluminum Indium) near2 amine with deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/06 10:05
S77	26	(Gallium Aluminum Indium) near2 (amino amide azido) with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/06 10:11
S78	5	dilute adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/06 10:40
S79	3	"6709703".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/06 10:15
S80	2	("4047496" "6218280").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/06 10:19
S81	9	US-5689123-\$.DID. OR US-5891790-\$.DID. OR US-5944913-\$.DID. OR US-6046096-\$.DID. OR US-6252287-\$.DID. OR US-6342405-\$.DID. OR US-6358822-\$.DID. OR US-6596079-\$.DID. OR US-6645885-\$.DID.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/06 12:38
S82	3	("6596079").URPN.	USPAT	OR	ON	2005/05/06 10:35
S83	6	(III Gallium Aluminum Indium) near2 (amino amine amide) same precursor and light adj emitting adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/06 12:40
S84	8	(III Gallium Aluminum Indium) near2 (amino amine amide) same precursor and nitride with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/06 11:09
S85	4	(III Gallium Aluminum Indium) near2 (amino amine amide) same precursor and III-v near2 nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/06 12:20
S86	2	("20020085973").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/05/06 12:30

S87	8	(reduc\$3 minimi\$5) adj ammon\$4 same vapor adj deposition	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/06 12:36
S88	23	(III Gallium Aluminum Indium) near2 (amino amine amide) same precursor and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/06 13:13
S89	34	organ\$3metal\$4 with single adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/06 13:21
S90	38	nitrogen adj (source precursor) with (GaI InN AlN)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/05/06 13:21
S91	5	dilute adj (nitride) near3 (coat\$3 layer film)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 11:25
S95	1	(nitride) near3 (coat\$3 layer film) and covelant\$4 adj bond\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 11:26
S97	45	(nitride) near3 (coat\$3 layer film) with covalent\$4 adj bond\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 11:38
S98	43	nitride with single adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 11:40
S99	48	nitride and single adj source and organometallic	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 13:26
S100	5	("5675028").URPN.	USPAT	OR	ON	2005/06/02 11:53
S101	1	("5650198").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/02 12:03
S102	19	("5464656").URPN.	USPAT	OR	ON	2005/06/02 13:25
S103	45	nitride and single adj source and III-v	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 13:30
S104	1	nitride and single adj source and III-v adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 13:30

S10 5	3	(III-V GaAs GaP InAs InP) with nitride adj (film layer cover\$3 coat\$3) and single adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:01
S10 6	17	(Ga and In and Al) same nitride adj (film layer cover\$3 coat\$3) and single adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:21
S10 7	2	"5209952".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:21
S10 8	6	("5209952").URPN.	USPAT	OR	ON	2005/06/02 15:03
S11 1	6	(GaInAsN GaInPN) and (layer film coat\$3) and precursor	USPAT	OR	ON	2005/06/02 17:03
S11 3	6	dilute adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/02 15:10
S11 4	1	"6660094"	USPAT	OR	ON	2005/06/02 17:03